

Application No.: 10/690,463

Docket No.: JCLA12280

In The Specification:

Please amend paragraph [0018] as follows:

[0018] Referring to FIG. 2 again, for an NMOS transistor in the two wing sections 12 of the multi-finger transistor 200, the drift region 250 thereof merely exists between the gate 210 and the source/drain region 220/230. For an NMOS transistor in the central section 10, however, the drift region 250 surrounds the drain region 230. In other words, in an NMOS transistor of the central section 10, the drift region 250 extends from the side boundary of the drain region 230 by a width "W", as shown in FIG. 2C. Since the drain region 230 in an NMOS transistor of the central section 10 is connected with the drift region 250 at two sides thereof, the curvature of junction depletion region of the drain region 230 can be reduced to result in a breakdown voltage higher than that of the drain region 230 of an NMOS transistor in the two wing sections 12.

In The Drawings:

Please substitute the attached clean drawing of Fig. 2 for the pending drawing of Fig. 2.

The amended portion is the addition of the reference numbers "10" and "12".